

**SPI 2019**

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# **Propagation Channel in Silicon in the Sub-THz Band for MPSoC**

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- **Introduction**
- **Propagation channel in V band**
- **Propagation channel in the Sub-THz band**
- **Conclusion**

# Introduction

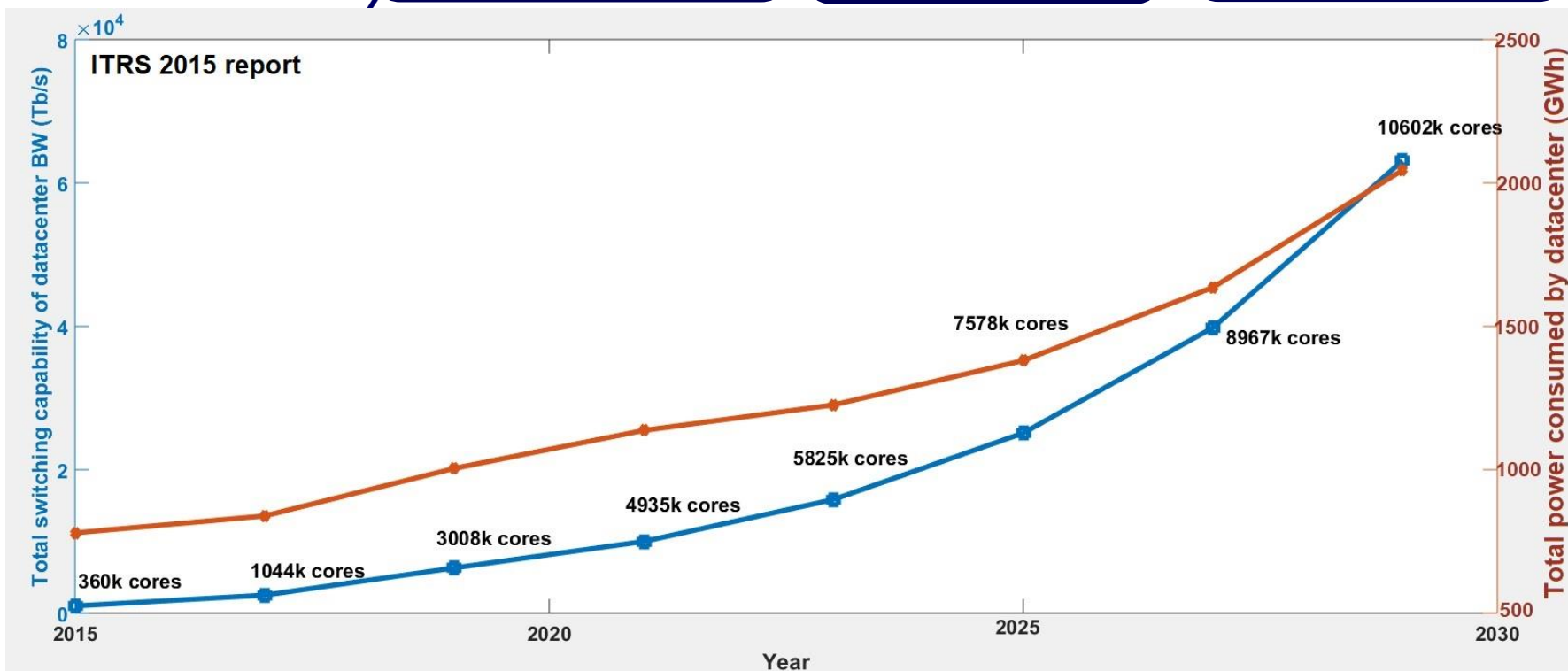
- **Multi processor system-on chip (MPSoC):**  
-> new applications :

Defense &  
Cyber-security

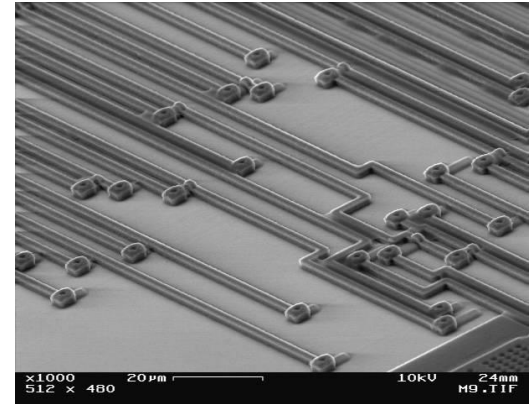
Artificial  
Intelligence (AI)

Multimedia  
applications

Internet of  
things (IoT)

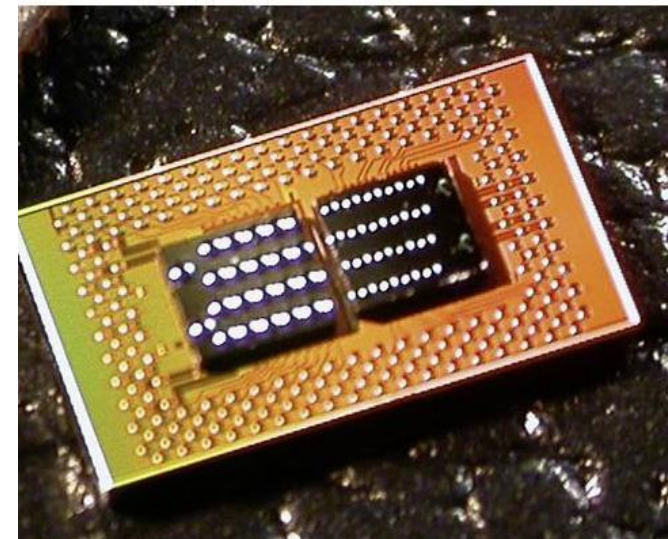


# Introduction



Classical metal interconnects (Intel)

- The classical metal interconnects constraints:
  - a) High latency.
  - b) High power consumption.
  - c) Routing complexities.
- Proposed alternatives :
  1. 3D interconnections.
  2. Optical interconnections.
  3. Carbone Nano-Tubes (CNT).
  4. RF interconnections .
  - 5. Wireless interconnections.**



Optical interconnections (IBM)

# Introduction

- **BBC** project (on-chip wireless **B**roadcast-**B**ased parallel **C**omputing)  
-> **W**ireless **I**nterconnects **N**etwork-**O**n-**C**hip (**WiNoC**):

## 1) Physical layer:

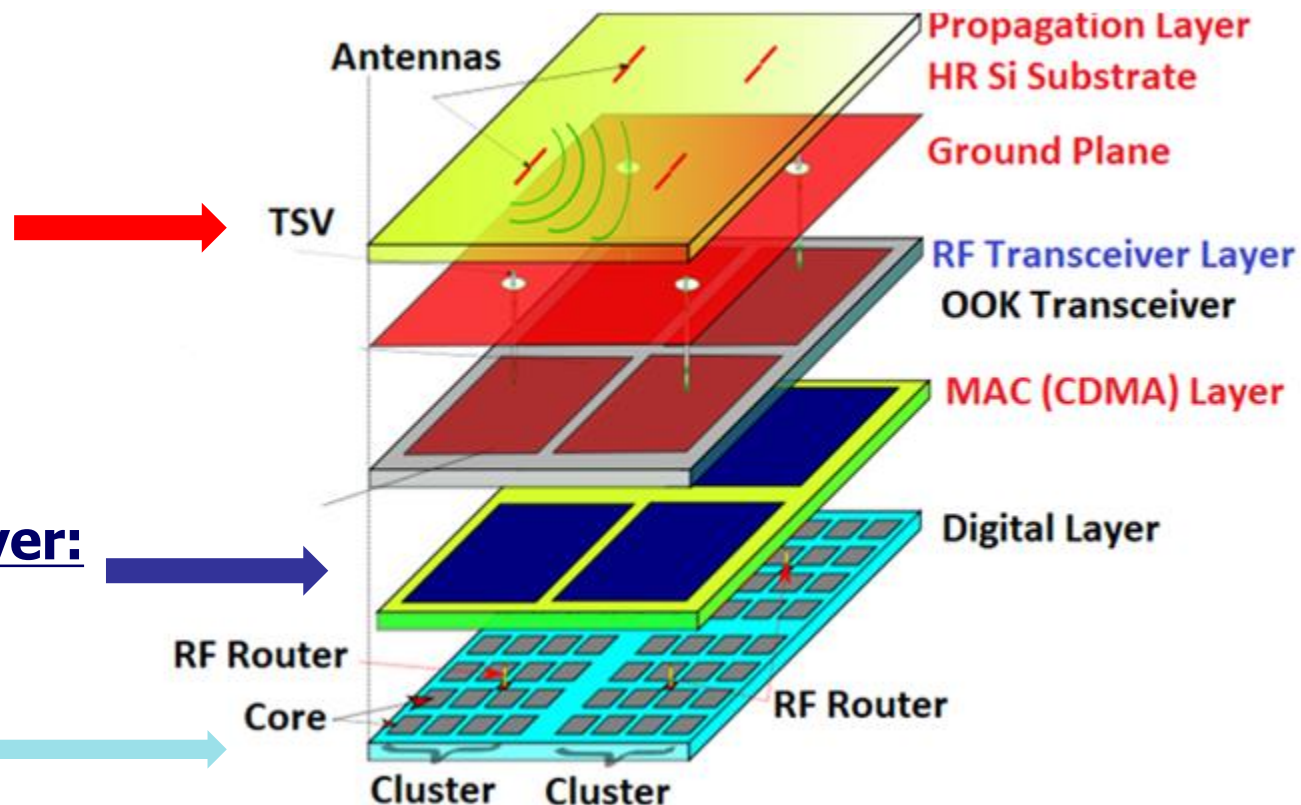
Propagation channel/  
Antennas/ Transceivers

## 2) Data link (MAC) layer:

Coding (CDMA)

## 3) Network layer :

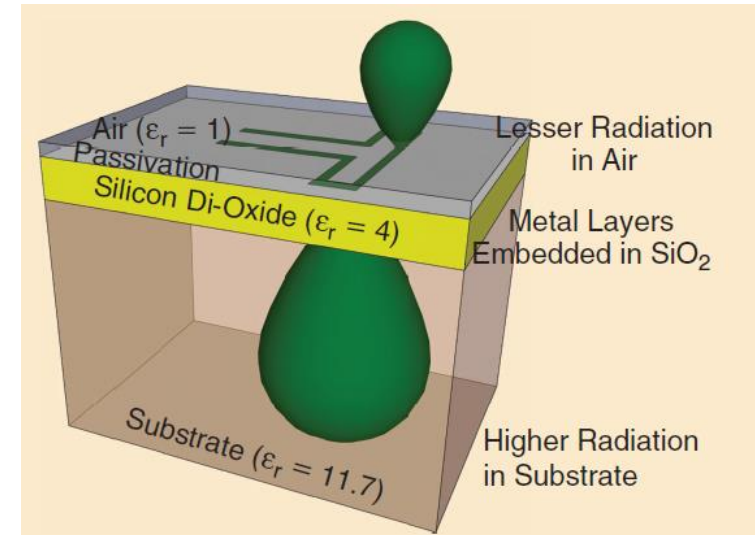
Routing algorithm





# Introduction

- WiNoC applications => **CMOS technology**  
=> **Silicon substrate**
- Problems due to the Silicon substrate:
  1.  $\epsilon_{r-Si} = 11,9$  & LR-Si\*:  $\rho = 10 \Omega.cm$  => low antenna efficiency
  2.  $\epsilon_{r-Si} = 11,9 \gg \epsilon_{air} = 1$  => reflections on **PMC\*\*** walls and a **resonant cavity**.



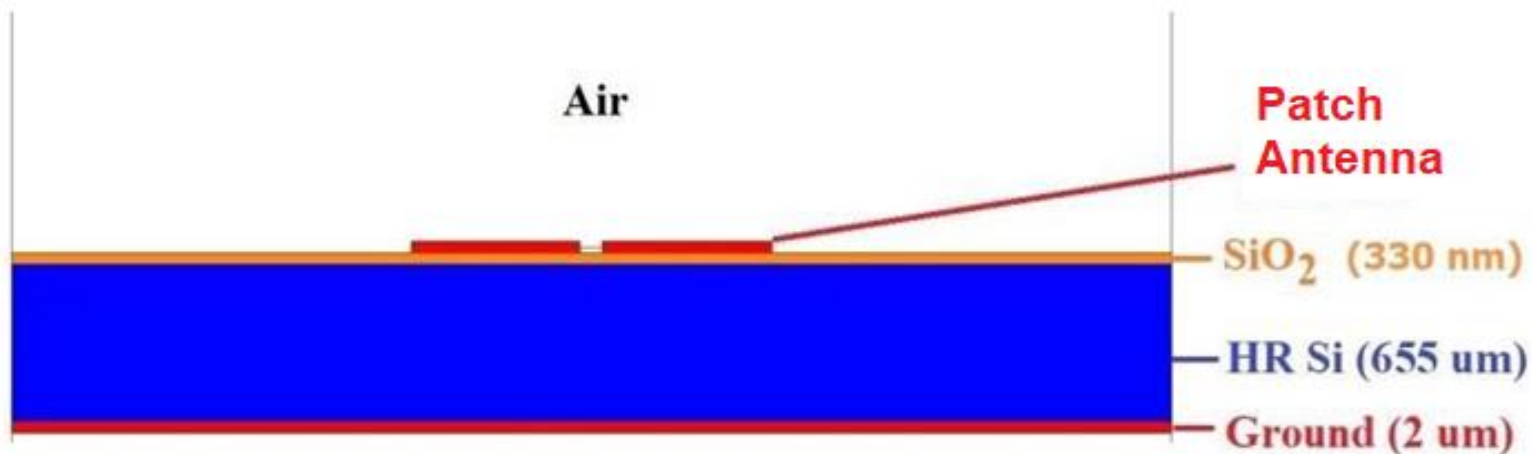
A radiation pattern for a typical integrated antenna on Silicon [1]

\* LR-Si: Low resistivity Silicon; \*\* PMC : Perfect Magnetic Conductor

[1] H. M. Cheema and A. Shamim, "The last barrier: on-chip antennas," *IEEE Microwave Magazine*, vol. 14, no. 1, pp. 79–91, Jan. 2013.

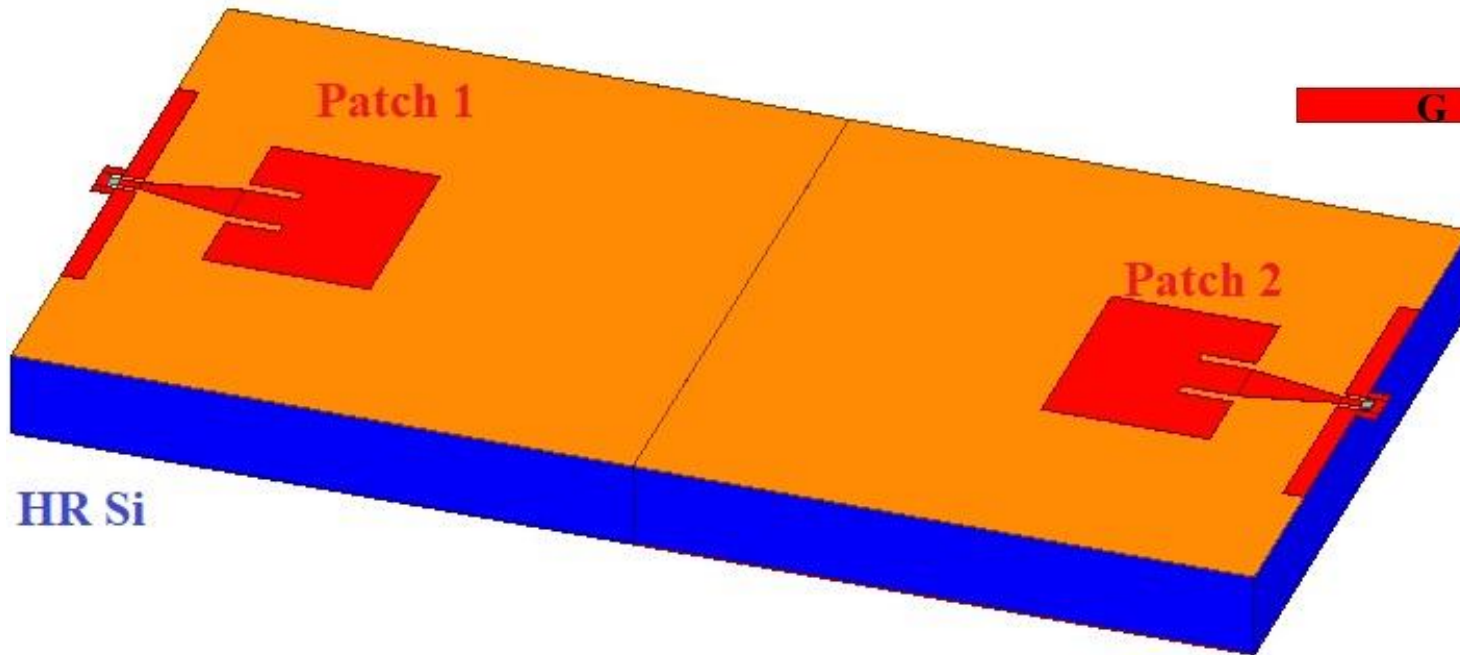
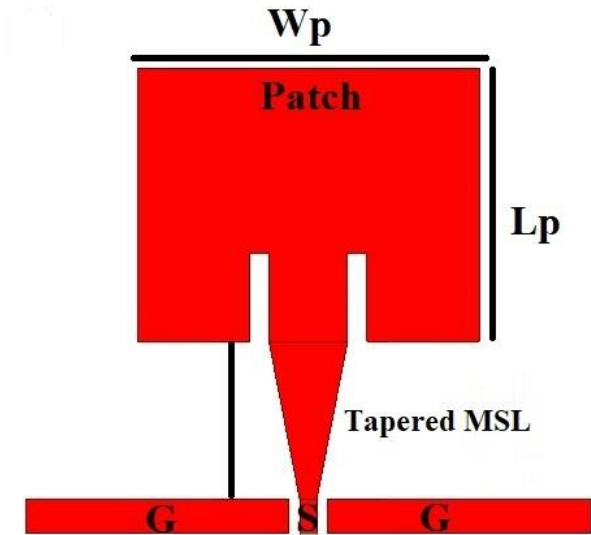
# Propagation channel in V band

- EM simulation (HFSS) and realization **structure:**
  - High-Resistivity Silicon (**HR-Si**) ( $\epsilon_{Si} = 11,9, H_{sub} = 655 \mu m$ )
  - A layer of 330 nm height of  $SiO_2$  ( $\epsilon_{SiO_2} = 4$ ).



# Propagation channel in V band

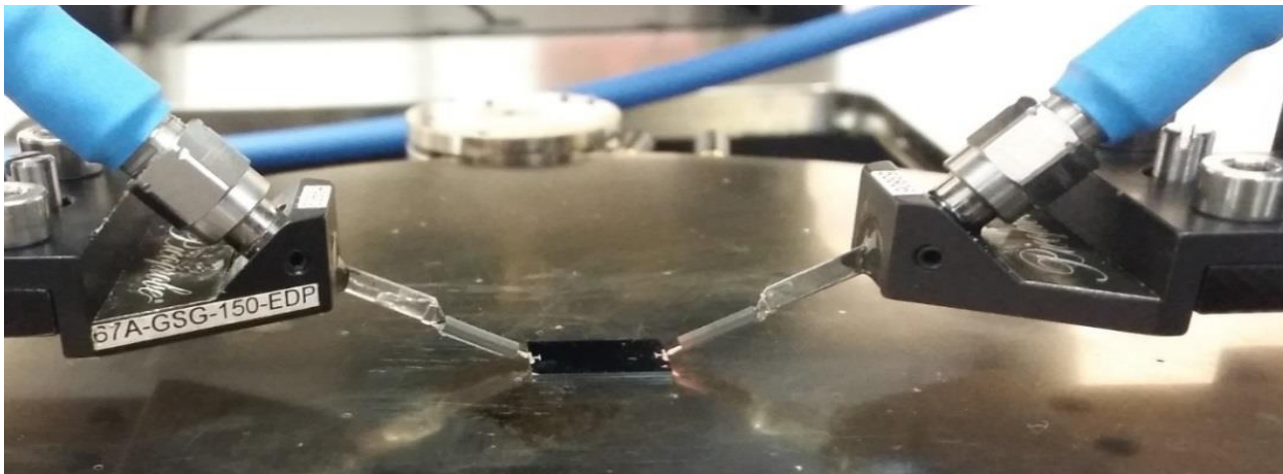
- Propagation channel between 2 patch antennas





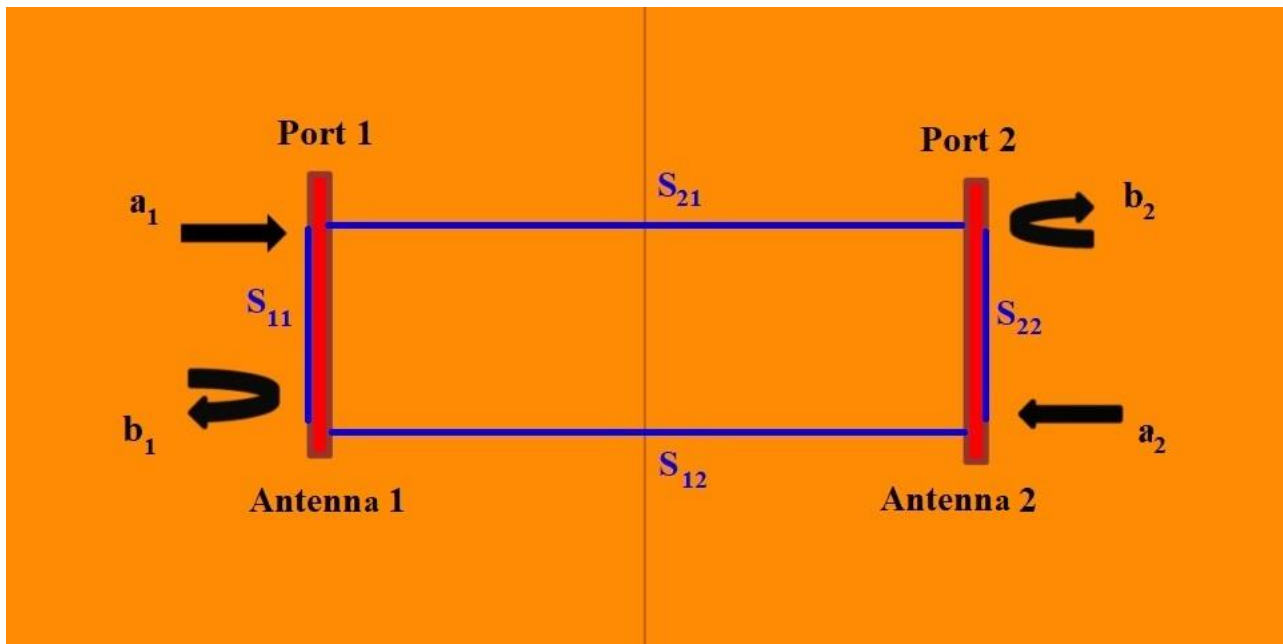
# Propagation channel in V band

- First prototype in **V band (40-75 GHz)**.
  - Realization @ GREMAN Laboratory -Tours.
  - Measurement with **GSG probes @ Lab-STICC – BREST**



# Propagation channel in V band

- Characterization through the S parameters:
  - Reflection:  $S_{11}$  or  $S_{22}$  :  $BW_{-10\text{ dB}}(\text{Hz}) \rightarrow$  *Matching bandwidth*
  - Transmission:  $S_{21}$  or  $S_{12}$  :  $BW_{-3\text{ dB}}(\text{Hz}) \rightarrow$  *Transmission bandwidth*

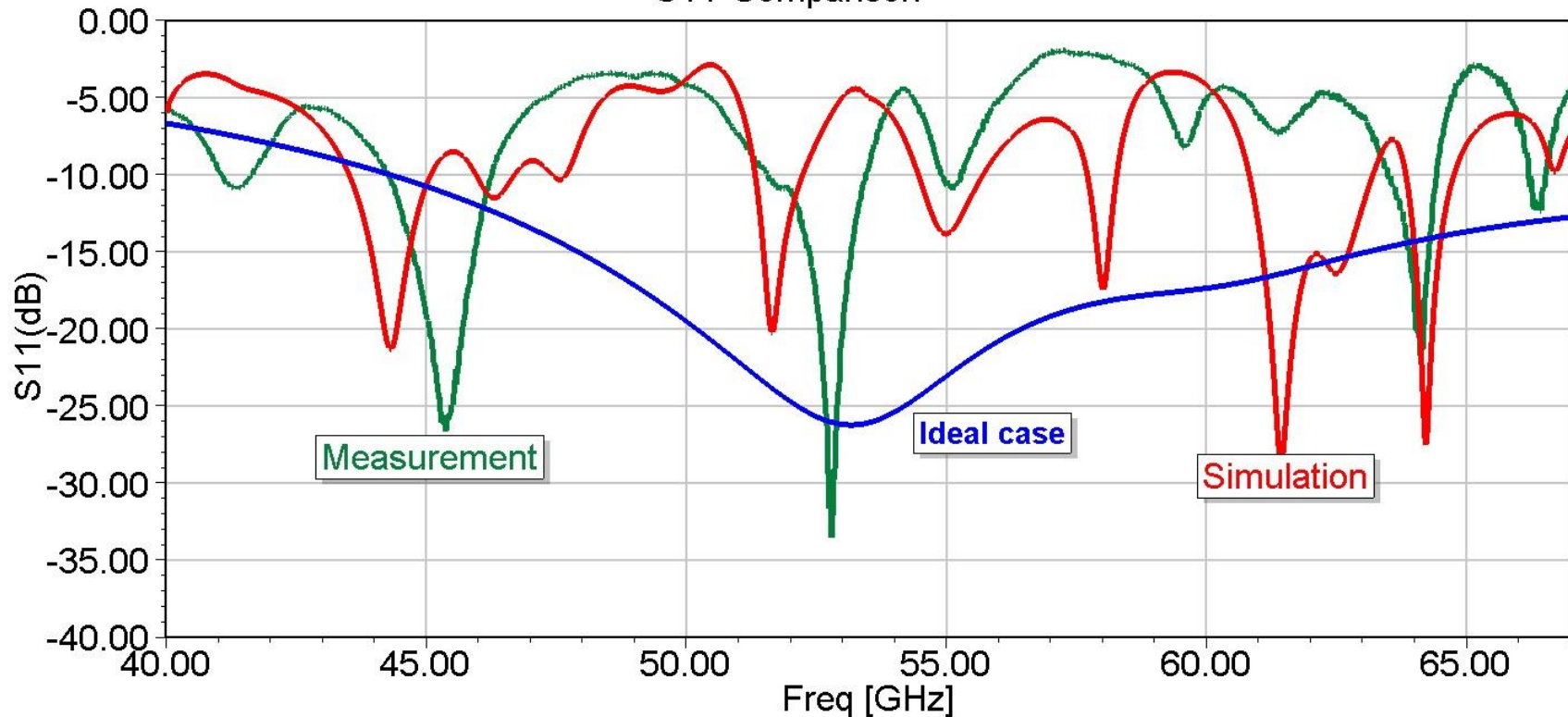


# Propagation channel in V band

- **Reflection coefficient ( $S_{11}$ ): Simulated vs. Measured:**
  - Multiple resonances.
  - Cause: cavity effects and multiple substrate modes.



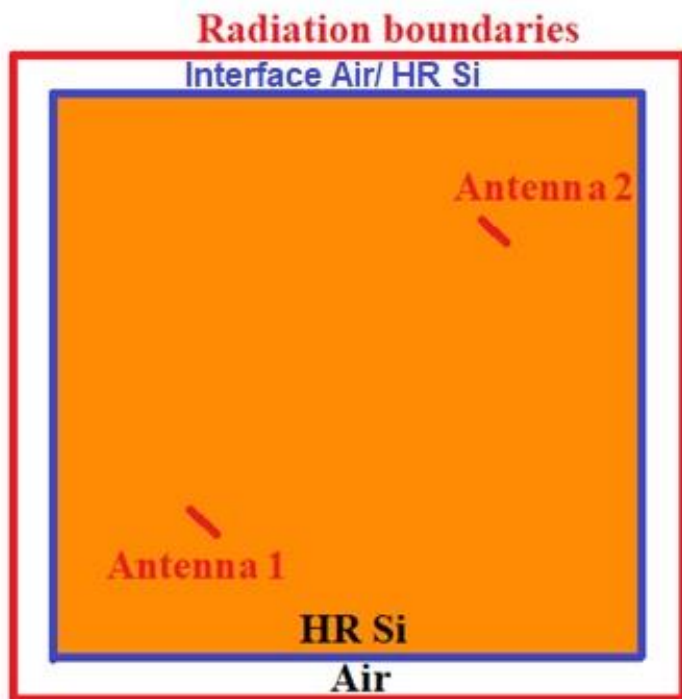
S11-Comparison



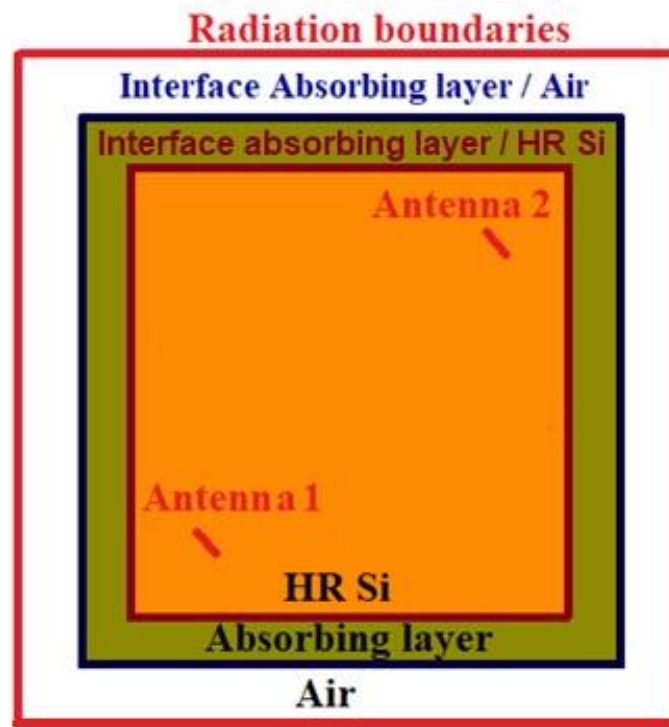
# Propagation channel in V band

- Solution to the cavity problem and the reflection on the air / Si interface :  
-> Absorbing layer surrounding the Si

## Case (1): Real



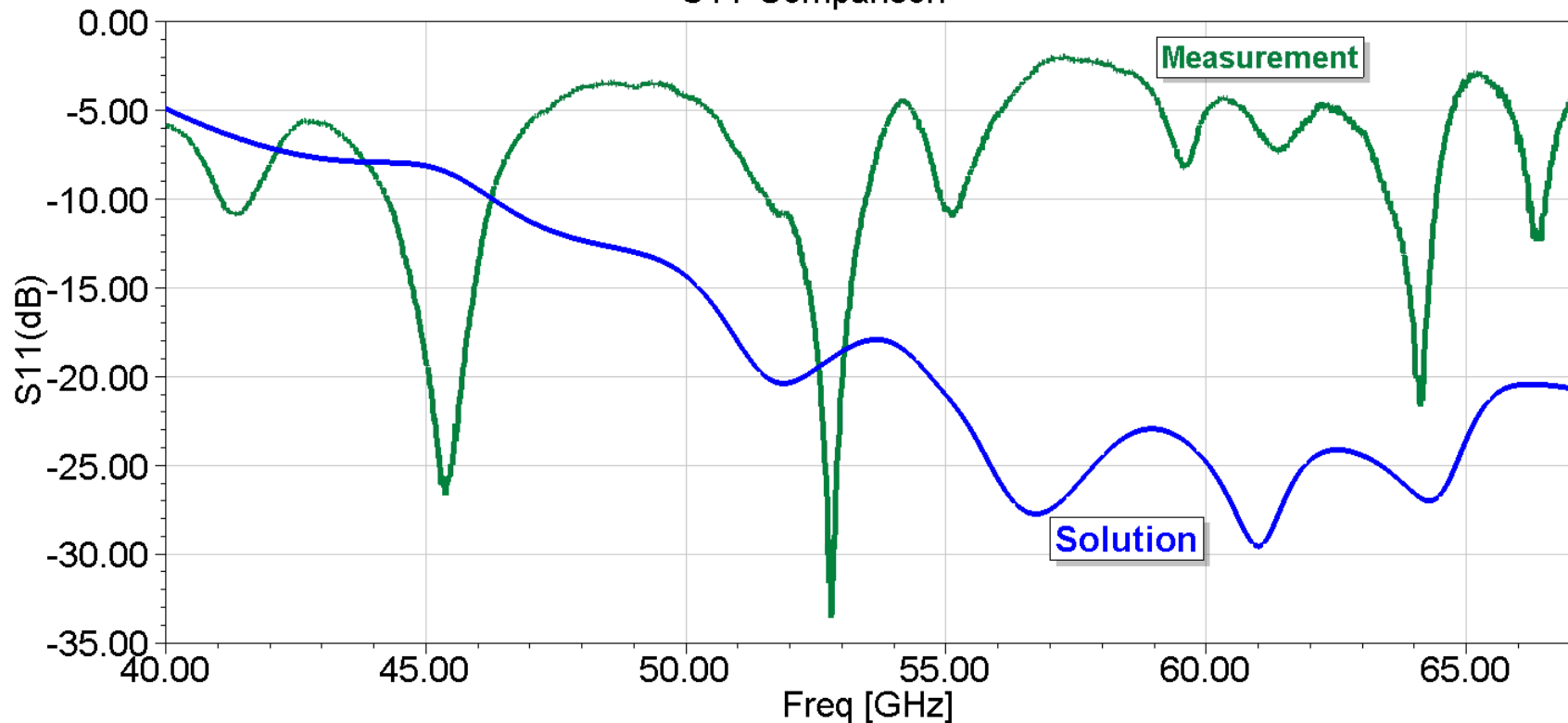
## Case (2): Solution



# Propagation channel in V band

- **Reflection coefficient ( $S_{11}$ ): Measured vs. Simulated :**
  - Multiple resonances -> Single resonance over a large matching BW.

S11-Comparison

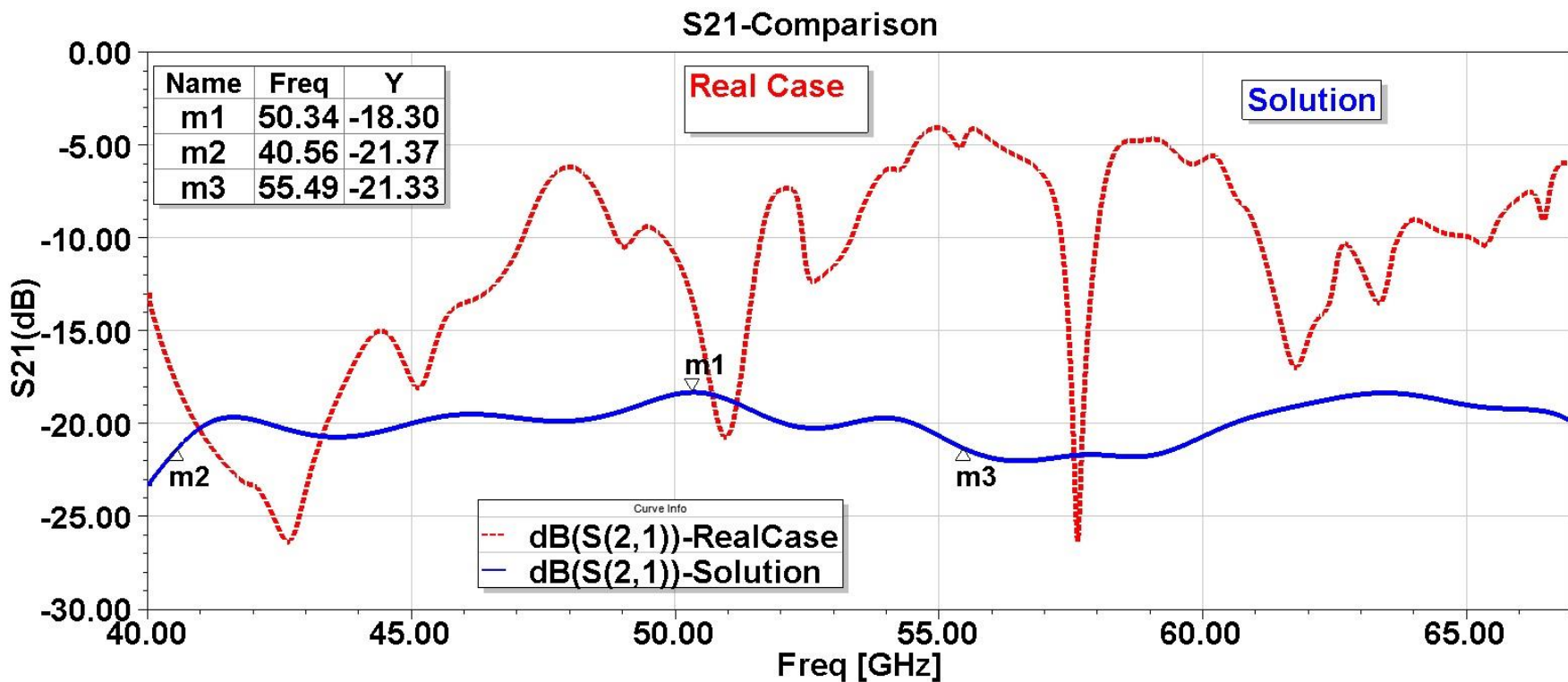


# Propagation channel in V band

- Transmission coefficient ( $S_{21}$ ): Simulated :

- Multiple transmission zeroes ->

Stable transmission over a large -3 dB BW .





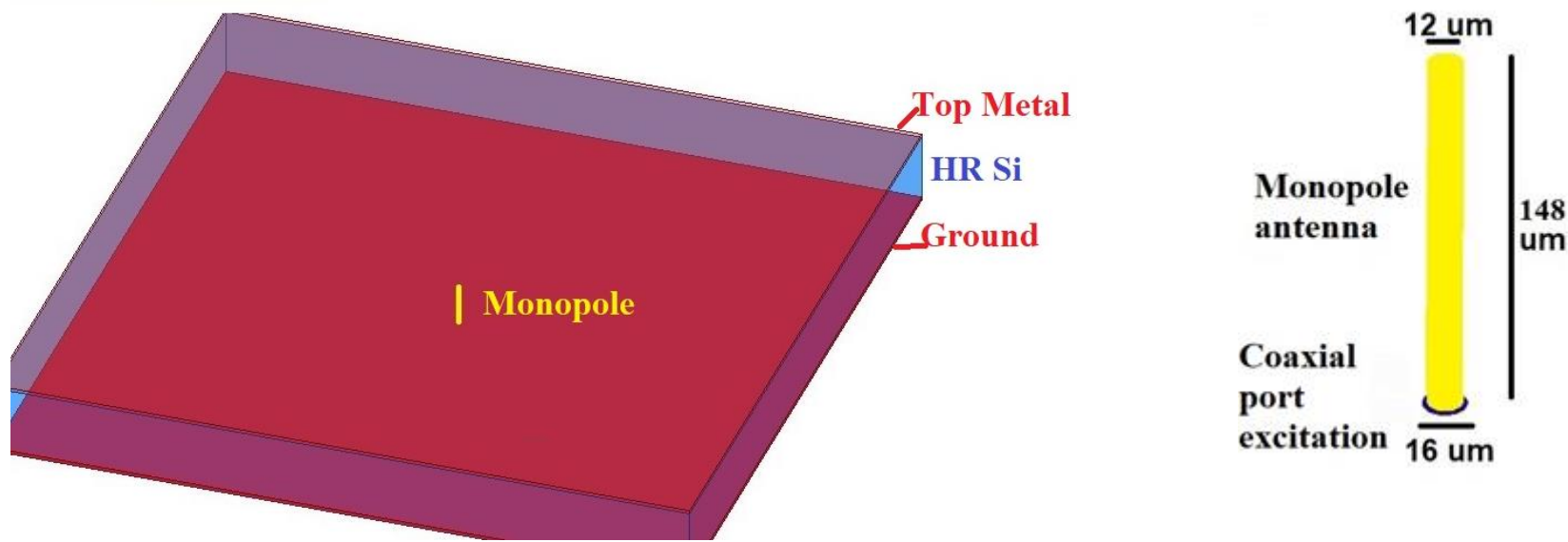
# Propagation channel in the Sub-THz band

- **Sub-THz band (30-300 GHz) =>**

1. High bandwidths : **10% = 20 GHz @ 200 GHz**

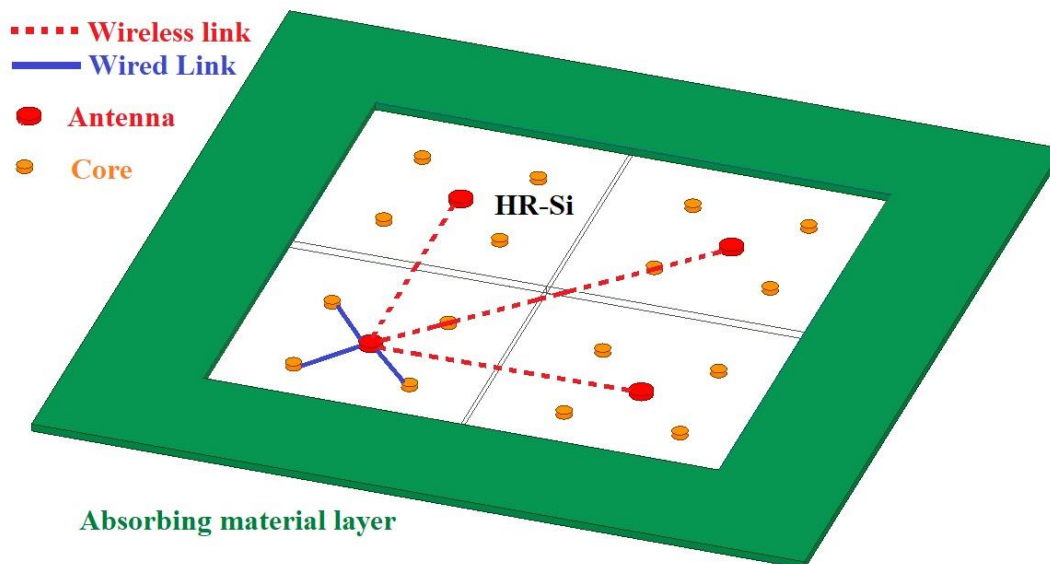
2. Reduced size of the antennas:

$\lambda \approx 435\mu\text{m}$  @ 200 GHz on Si -> **Vertical monopoles** embedded in the substrate -> **Multicast + Broadcast**



# Propagation channel in the Sub-THz band

- Surrounding absorbing layer => No cavity problem



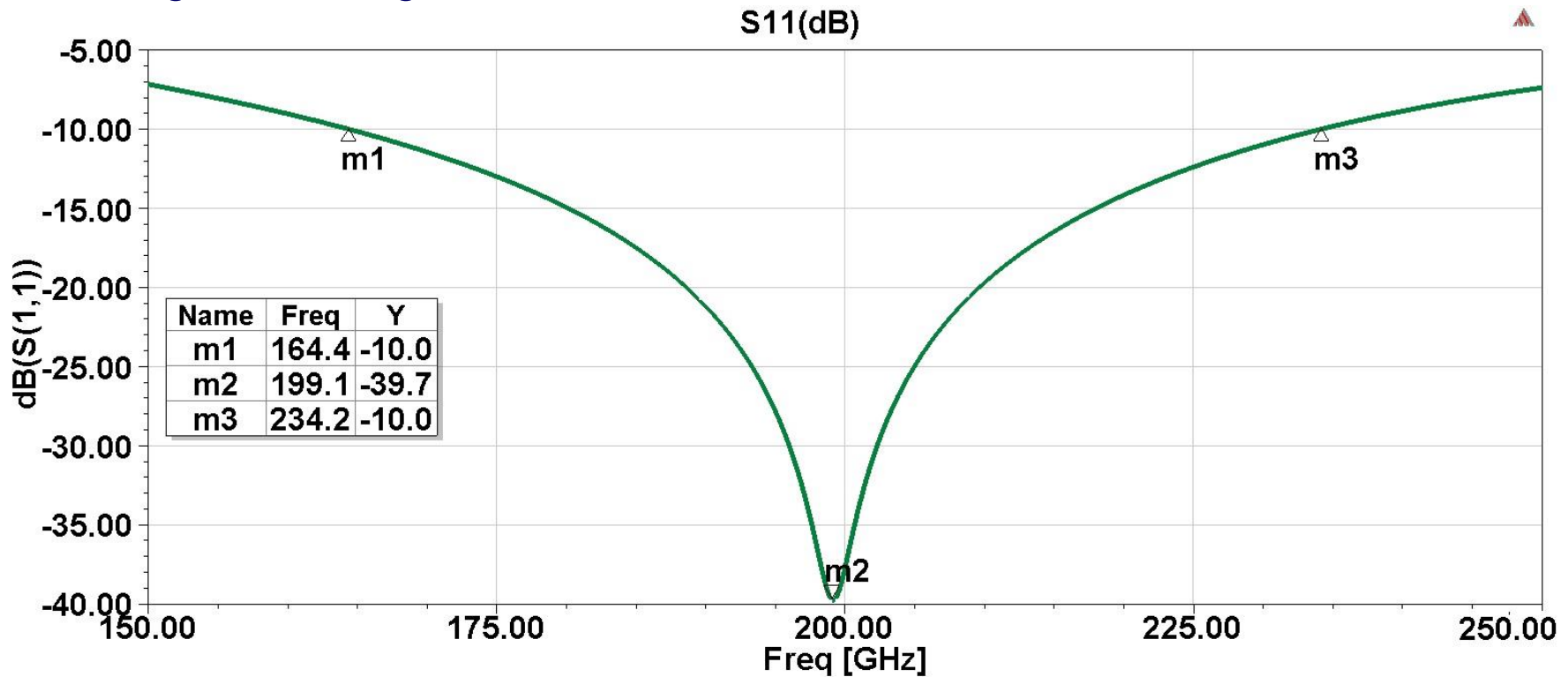
- Two metallic planes (top and bottom) => HR Si as a **2D guiding media** + **No EMC** problem



# Propagation channel in the Sub-THz band

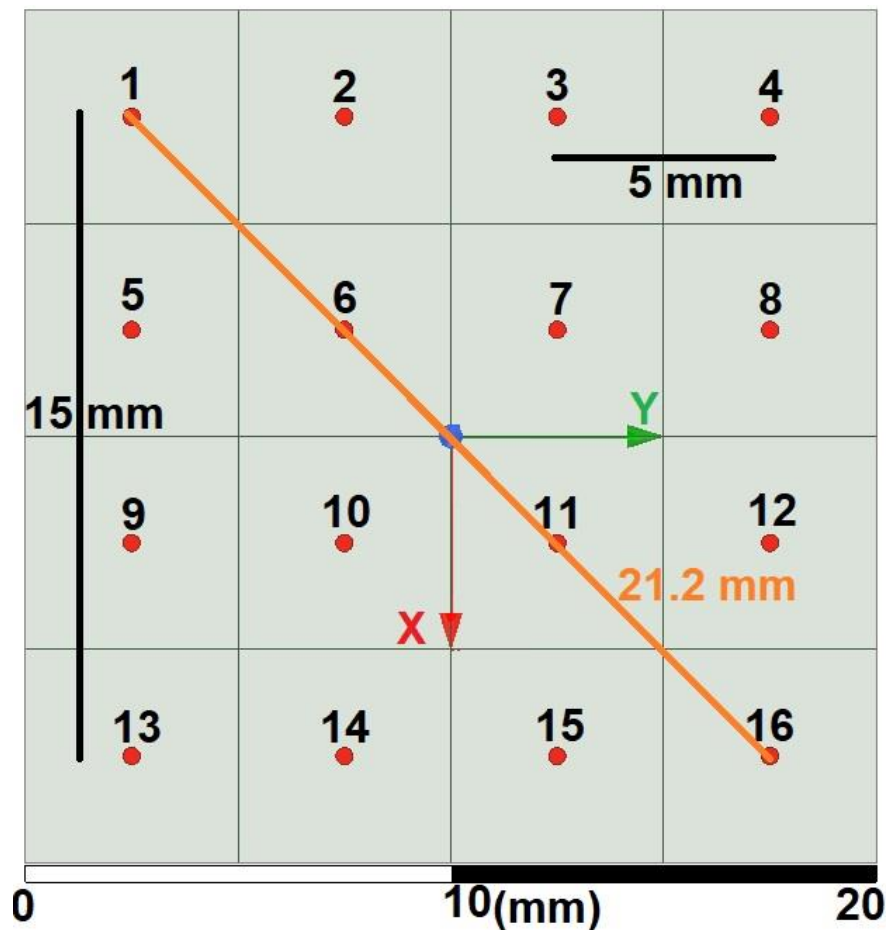
## • Reflection coefficient ( $S_{11}$ ): Simulated :

- Single resonance.
- Large matching BW : 70 GHz ( $\approx 35\%$ )



# Propagation channel in the Sub-THz band

- **A realist Many-Core scenario:**
  - Squared mesh with 16 monopoles
  - 1 Antenna per cluster
  - 8 cores per cluster => 128 cores  
(Used by: Intel, NVIDIA, Tileria ...)



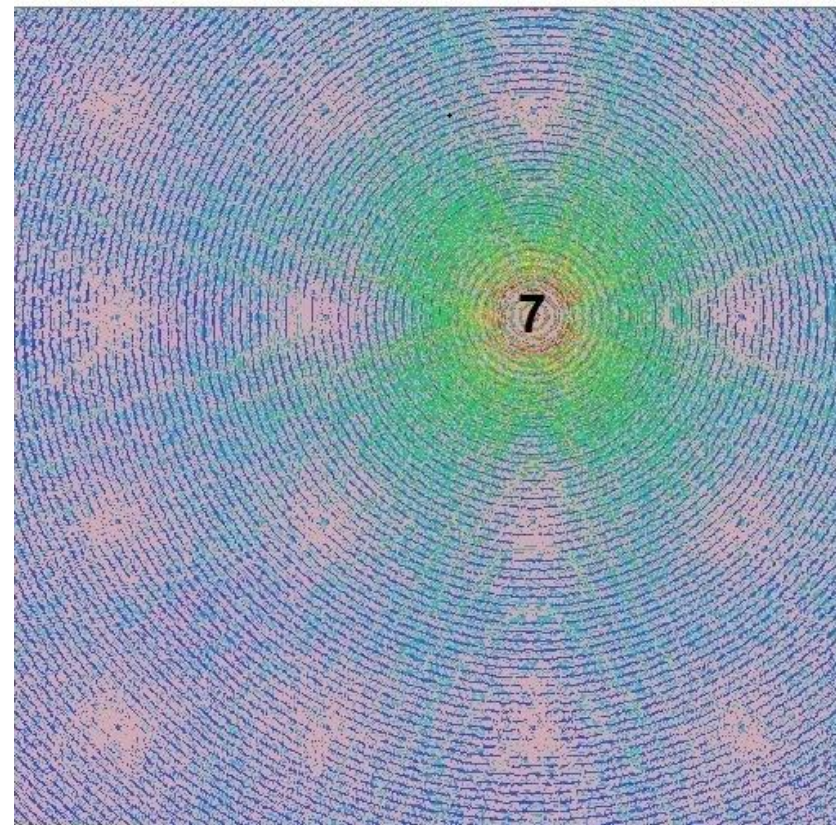


# Propagation channel in the Sub-THz band

Electric field distribution of the antenna #7

@200 GHz

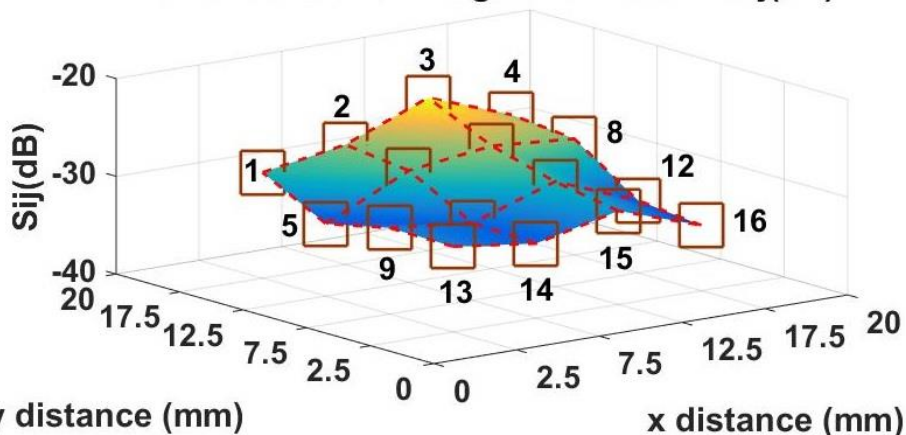
1. Convenient for Broadcast /Multicast
2. Dependence on the **antennas placement and the distance** of separation



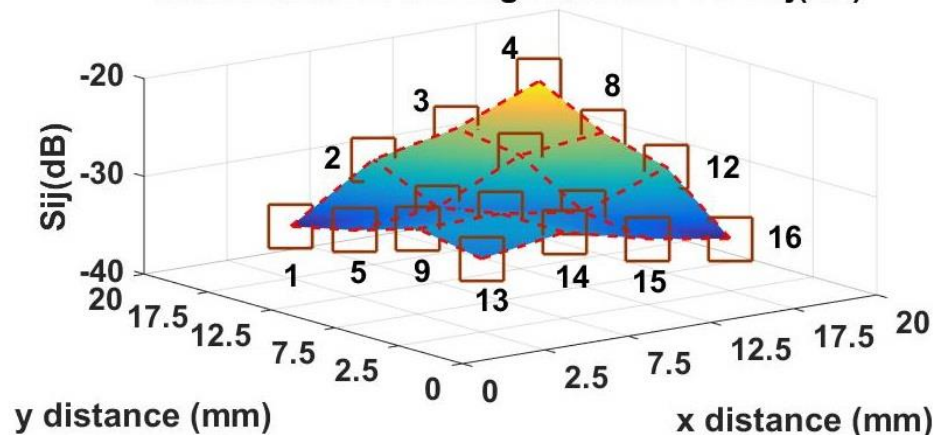
# Propagation channel in the Sub-THz band

Effect of the antennas placement and the distance on the signal intensity

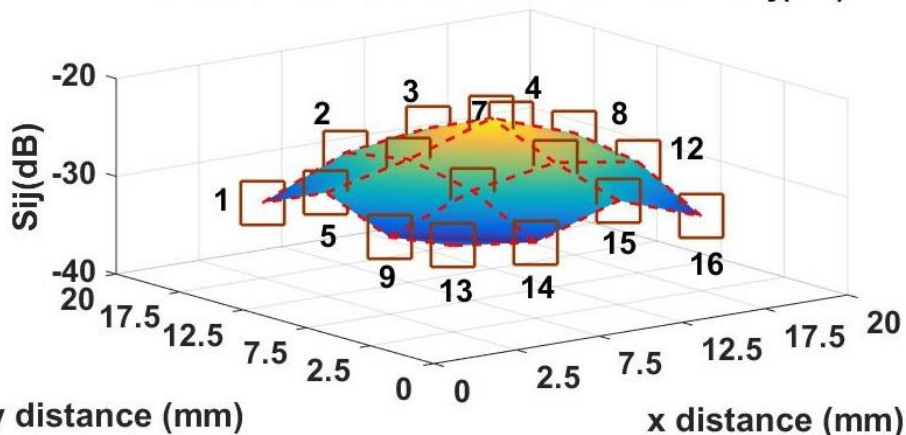
Interactions of the edge antenna #3: S3j(dB)



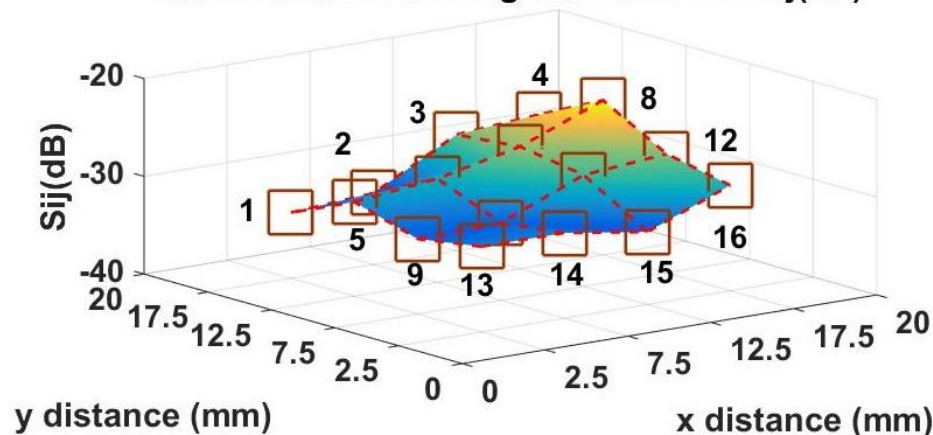
Interactions of the edge antenna #4: S4j(dB)



Interactions of the center antenna #7: S7j(dB)



Interactions of the edge antenna #8: S8j(dB)

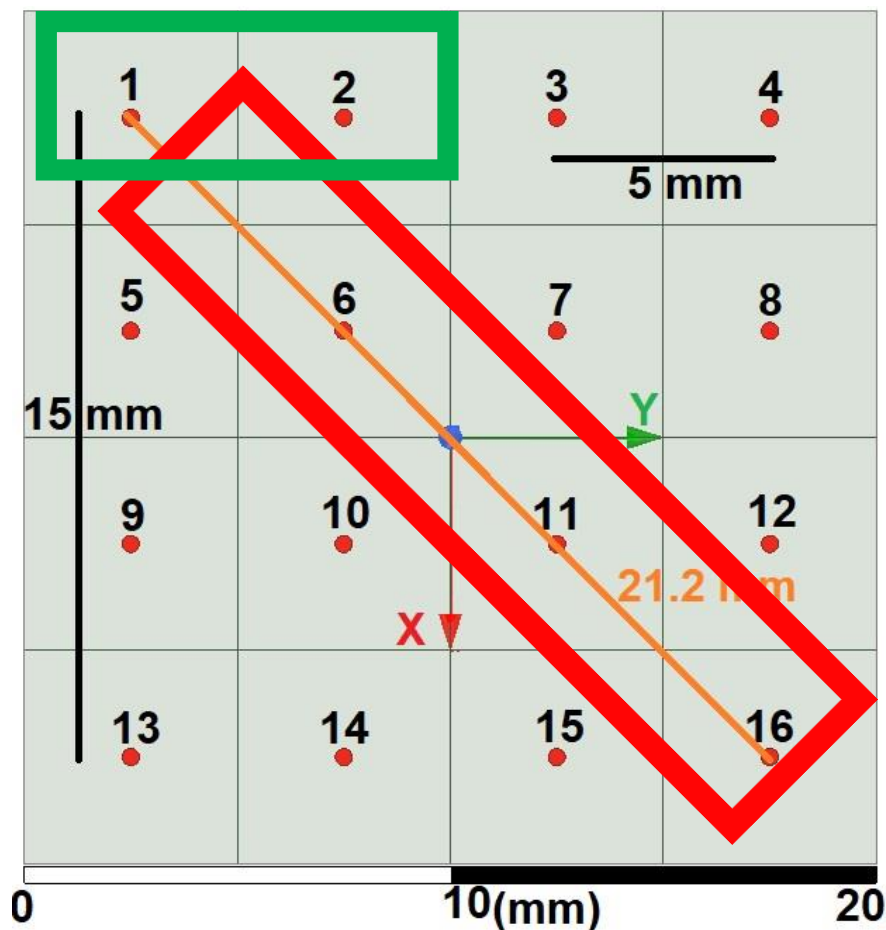




# Propagation channel in the Sub-THz band

Best Case scenario : highest levels and largest -3dB-BW between the closest antennas (ex. 1 & 2 or equivalent) with a distance of separation of 5 mm.

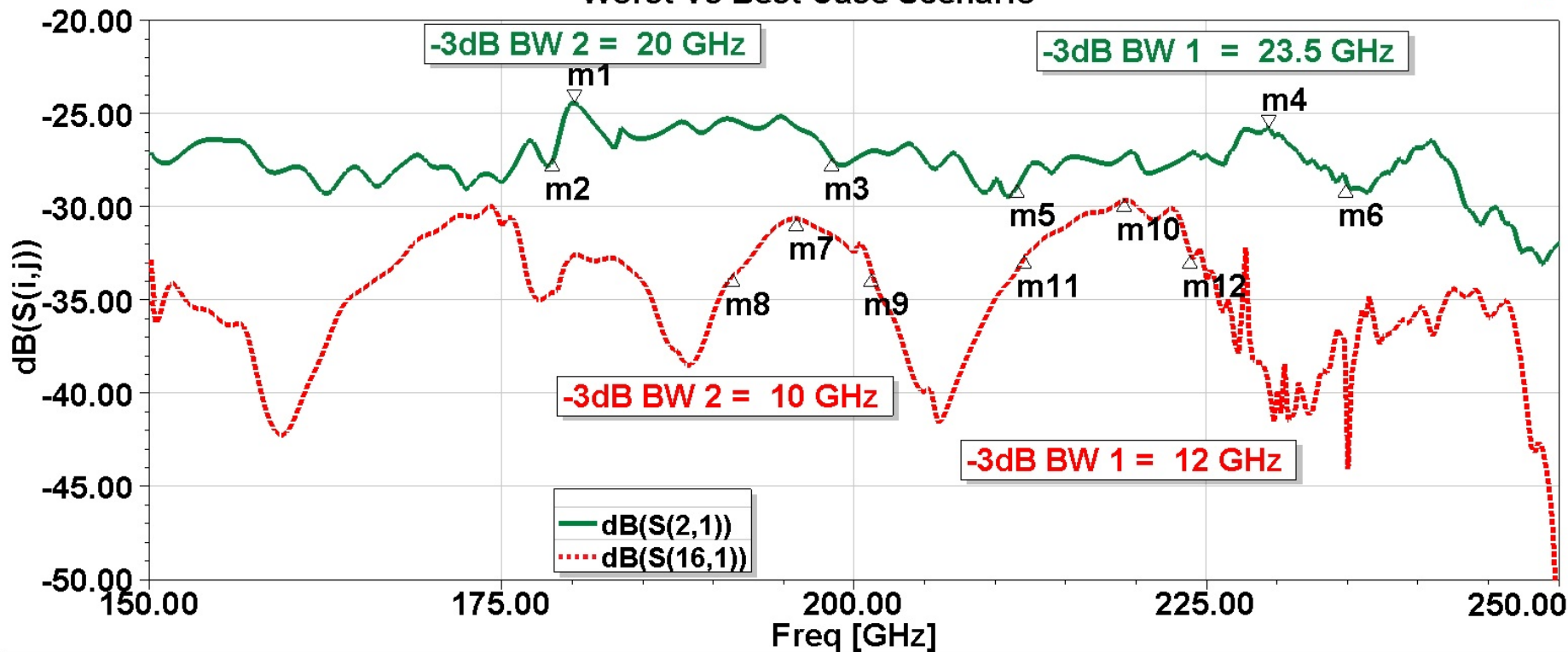
Worst-case scenario: between the farthest antennas i.e. on the diagonals (1 & 16 or 4 & 13) with a distance of separation of 21.2 mm.



# Propagation channel in the Sub-THz band

## Transmission coefficient ( $S_{ij}$ ): Simulated :

Worst Vs Best Case Scenario



$-3\text{dB BW } 2 = 20 \text{ GHz}$   $-3\text{dB BW } 1 = 23.5 \text{ GHz}$   $-3\text{dB BW } 2 = 10 \text{ GHz}$   $-3\text{dB BW } 1 = 12 \text{ GHz}$

Name	Freq	Y	Name	Freq	Y	Name	Freq	Y	Name	Freq	Y
m1	180.25	-24.47	m4	229.50	-25.86	m7	196.00	-30.66	m10	219.25	-29.65
m2	178.65	-27.47	m5	211.60	-28.86	m8	191.47	-33.66	m11	212.14	-32.65
m3	198.46	-27.47	m6	234.98	-28.86	m9	201.31	-33.66	m12	223.91	-32.65

# Propagation channel in the Sub-THz band

- Data rate comparable to the state of the art of the WiNoC
- Coding can be optimized in both cases

Case	-3dB BW1 (GHz)	-3dB BW2 (GHz)	Possible data rate (Gbps) For both BW *	Possible data rate (Gbps) For BW1 only **
Best Case Scenario	23,5	20	> 32	> 16
Worst Case Scenario	12	10	> 16	> 8

\* By a frequency multiplexing, possible benefit of both bandwidths

\*\* Using only the largest bandwidth

## Conclusion

1. The advantages of the WiNoC antennas in the EHF band:  
**high bandwidth** with a **minimal size**.
2. **The cavity** problems :  
**Multiple resonances** and **transmission zeros**.
3. **Proposed solutions:**
  - A. Addition of an **absorption layer**
  - B. **Two metallic planes** to avoid **EMC influences**
  - C. **HR-Si** as a **propagation medium**
  - D. Additional improvement through the vertical **monopole antennas**.

## Perspectives

1. Proof of concept: Measurement of the realized **absorbing layer circuits** in **Q** and **V band**.
2. **Task Mapping** at the **coding/routing** levels based on the **attenuation maps**.
3. Combination of **RF models and digital techniques** and evaluation of the **complete proposed WiNoC solution**.

# Questions

**Thank you for your attention**



**Work performed on the High Performance Computing Cluster(HPC) at Lab-STICC:**

<https://www.univ-brest.fr/plateformes-technologiques/menu/nos-plates-formes/TECHYP>